

TOSHIBA**MG150J2YS50**

TOSHIBA GTR Module Silicon N Channel IGBT

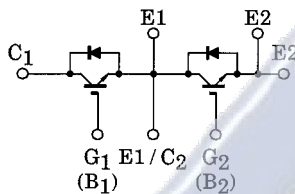
MG150J2YS50

High Power Switching Applications

Motor Control Applications

- The electrodes are isolated from case
- High input impedance
- Includes a complete half bridge in one package
- Enhancement-mode
- High speed : $t_f = 0.30\mu s$ (Max) ($I_C = 150A$)
 $t_{rr} = 0.15\mu s$ (Max) ($I_F = 150A$)
- Low saturation voltage : $V_{CE(sat)} = 2.70V$ (Max) ($I_C = 150A$)

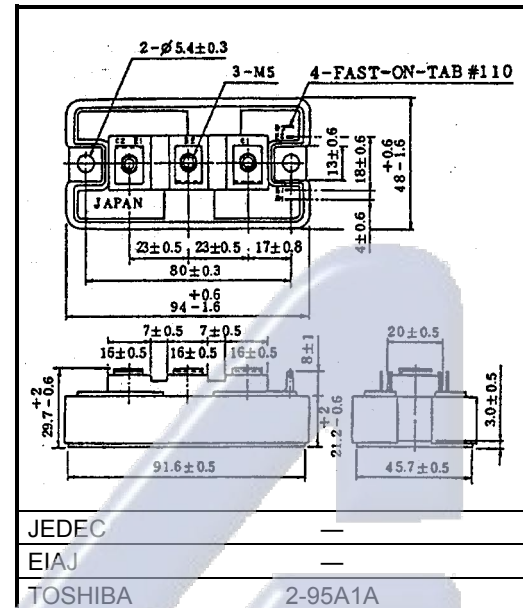
Equivalent Circuit



Maximum Ratings ($T_a = 25^\circ C$)

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	600	V
Gate-emitter voltage		V_{GES}	± 20	V
Collector current	DC	I_C	150	A
	1ms	I_{CP}	300	
Forward current	DC	I_F	150	A
	1ms	I_{FM}	300	
Collector power dissipation ($T_c = 25^\circ C$)		P_C	780	W
Junction temperature		T_j	150	$^\circ C$
Storage temperature range		T_{stg}	$-40 \sim 125$	$^\circ C$
Isolation voltage		V_{isol}	2500 (AC 1 min.)	V
Screw torque (Terminal / mounting)		—	3 / 3	N·m

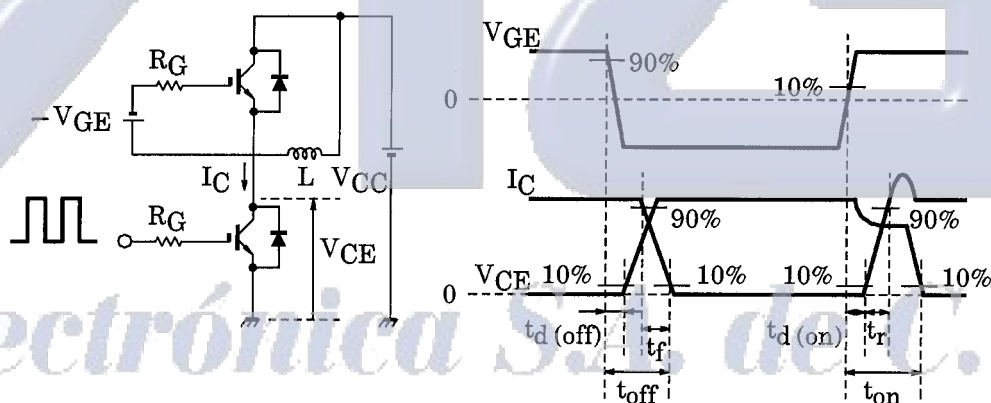
Unit: mm

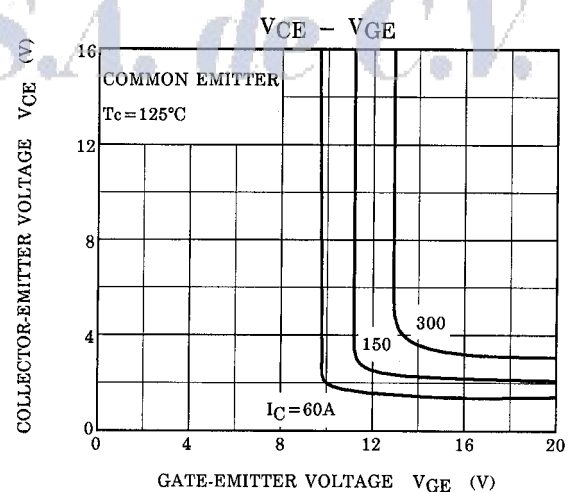
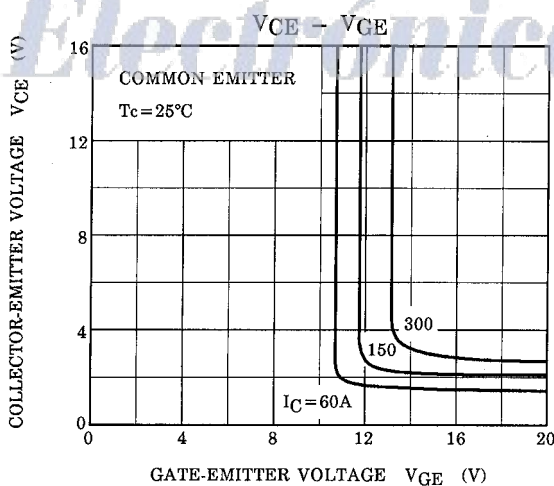
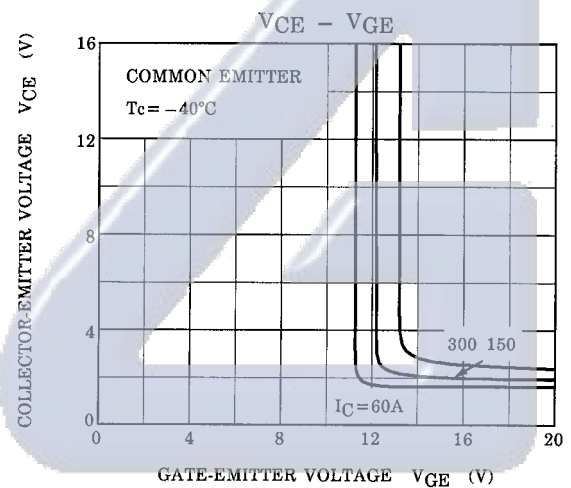
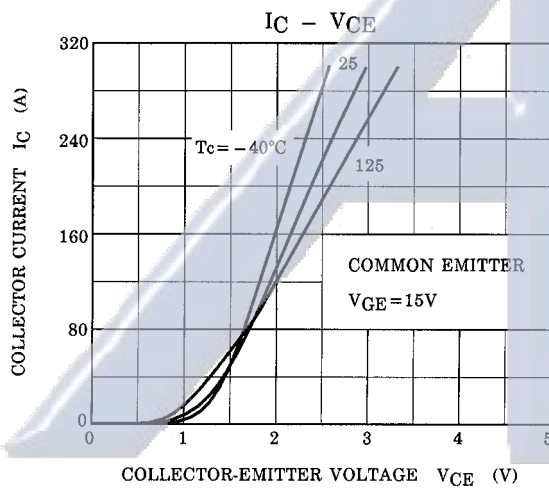
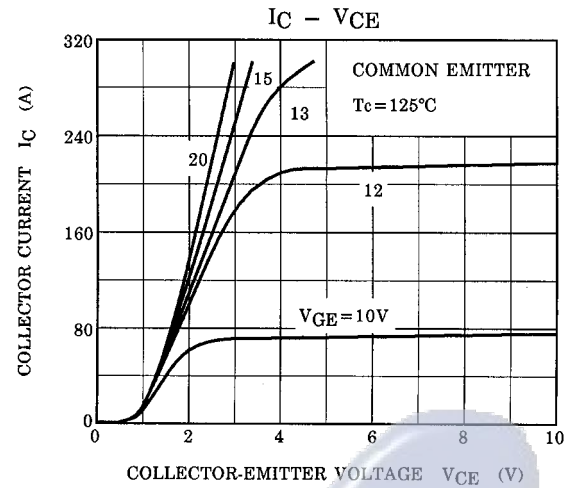
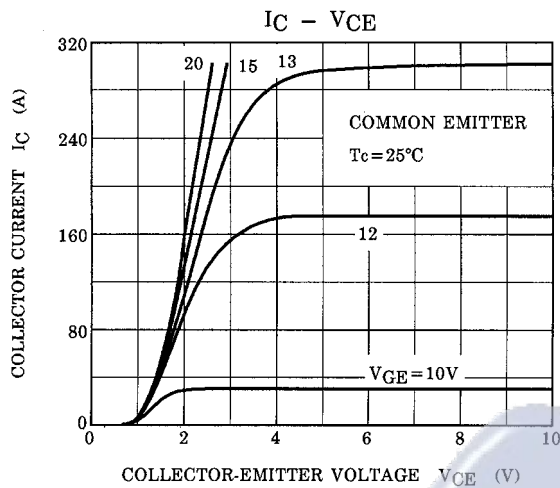


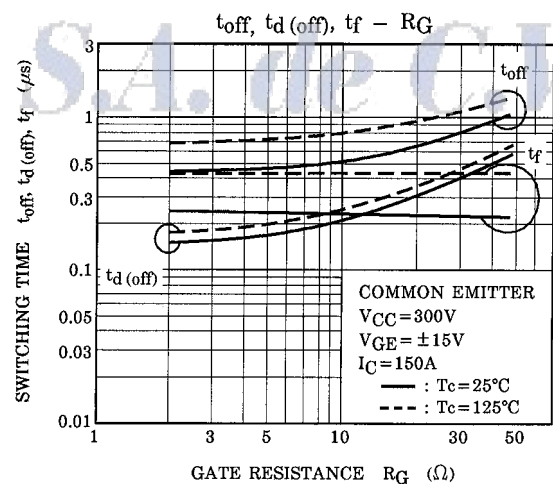
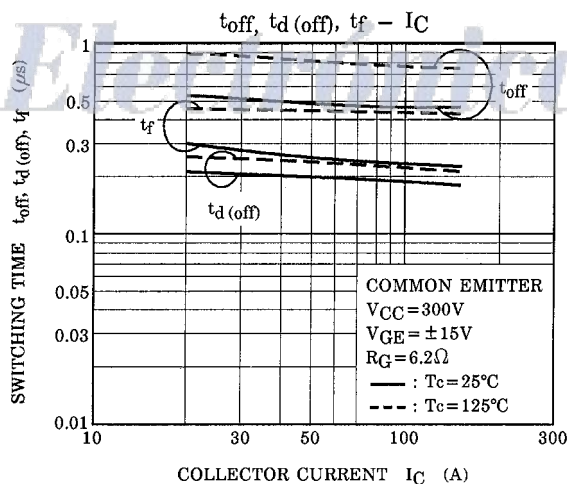
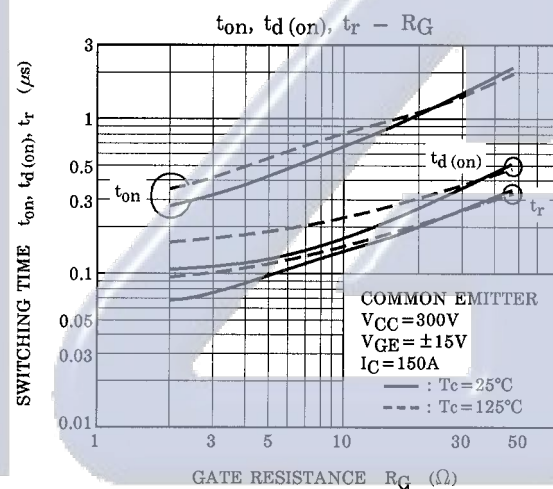
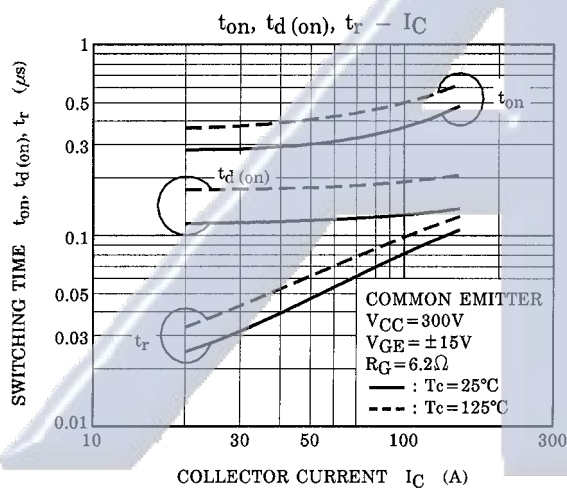
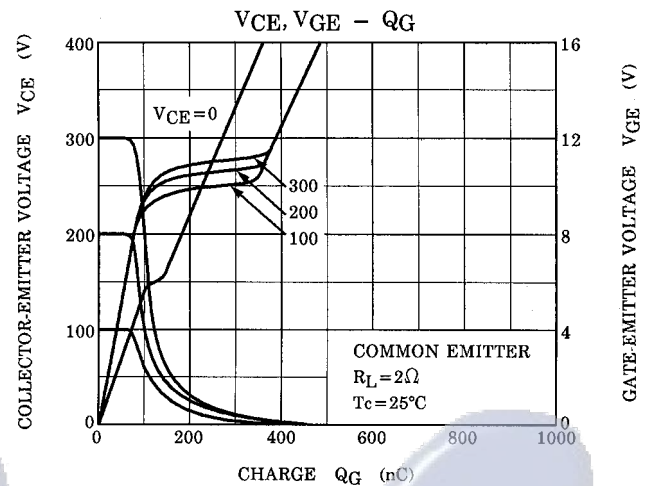
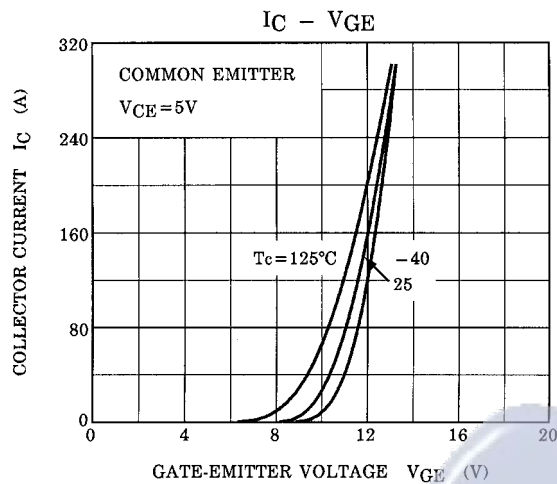
TOSHIBA**MG150J2YS50****Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector cut-off current		I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	2.0	mA
Gate-emitter cut-off voltage		$V_{GE(off)}$	$I_C = 15mA, V_{CE} = 5V$	5.0	7.0	8.0	V
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 150A, V_{GE} = 15V$	—	2.10	2.70	V
Input capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	14200	—	pF
Switching time	Turn-on delay time	$t_{d(on)}$	Inductive load $V_{CC} = 300V$ $I_C = 150A$ $V_{GE} = \pm 15V$ $R_G = 6.2\Omega$ (Note 1)	—	0.15	0.30	μs
	Rise time	t_r		—	0.15	0.30	
	Turn-on time	t_{on}		—	0.50	1.00	
	Turn-off delay time	$t_{d(off)}$		—	0.20	0.40	
	Fall time	t_f		—	0.15	0.30	
	Turn-off time	t_{off}		—	0.50	1.00	
Forward voltage		V_F	$I_F = 150A, V_{GE} = 0$	—	2.30	3.00	V
Reverse recovery time		t_{rr}	$I_F = 150A, V_{GE} = -10V$ $di/dt = 200A/\mu s$	—	0.08	0.15	μs
Thermal resistance		$R_{th(j-c)}$	Transistor stage	—	—	0.16	$^{\circ}C/W$
			Diode stage	—	—	0.35	

Note 1: Switching time test circuit & timing chart



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